



# DMN3032LFDBWQ

### DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
2014	30mΩ @ V <sub>GS</sub> = 10V	5.5A
30V	$42m\Omega @ V_{GS} = 4.5V$	4.7A

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and ideal for use in:

- Body Control Electronics
- Power Management Functions
- DC-DC Converters

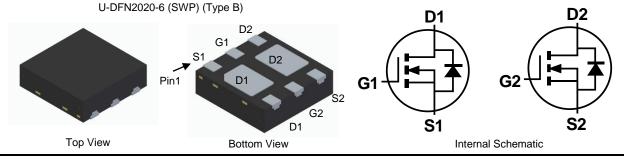
# **Features and Benefits**

- 100% Unclamped Inductive Switching—Ensures More Reliable
  and Robust Application
- Low On-Resistance—Minimizes Power Losses
- Low Gate Charge—Minimizes Switching Losses
- Small Form Factor Low-Profile Package—Increased Power Density
- Sidewall Plated for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3032LFDBWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Terminals Connections: See Diagram Below
- Weight: 0.007 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3032LFDBWQ-7	U-DFN2020-6 (SWP) (Type B)	3000/Tape & Reel
DMN3032LFDBWQ-13	U-DFN2020-6 (SWP) (Type B)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

Date Code Key				NW	M I	NW = Prod YM = Date Y = Year (e M = Month	Code Mark ex: H = 202	king 0)	le			
Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н		J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-Source Voltage		Vgss	±20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10V$ State $T_A = +25^{\circ}C$ $T_A = +75^{\circ}C$			ID	5.5 4.4	А
Maximum Continuous Body Diode Forward Curre	nt (Note 6)	ls	1.7	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	I <sub>DM</sub>	30	A	
Avalanche Current (Note 7) L = 0.1mH		las	12	A	
Avalanche Energy (Note 7) L = 0.1mH	Eas	7.7	mJ		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.82	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	153	°C/W
Total Power Dissipation (Note 6)		PD	1.37	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	91	°C/W
Thermal Resistance, Junction to Case (Note 6)		Rejc	30	C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

						1	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)					1	F	
Drain-Source Breakdown Voltage	BVDSS	30	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS		_	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +150°C (Note 9)	IDSS		_	100	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(th)	1.0	—	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Basion		24	30	mΩ	$V_{GS} = 10V, I_D = 5.8A$	
	RDS(ON)		30	42	11122	$V_{GS} = 4.5V, I_D = 4.8A$	
Diode Forward Voltage	Vsd	_	0.7	1.2	V	$V_{GS} = 0V$ , $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	500	—	pF		
Output Capacitance	Coss	_	52	—	pF	Vps = 15V, Vgs = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	—	44	—	рF		
Gate Resistance	Rg	—	2.3	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		5.0	—	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	—	10.6	—	nC		
Gate-Source Charge	Q <sub>gs</sub>		1.3	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.8A	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.8	-	nC		
Turn-On Delay Time	td(on)	_	2.2	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	2.6	—	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	tD(OFF)	_	9.7	_	ns	$R_L = 2.6\Omega, R_G = 3\Omega$	
Turn-Off Fall Time	tF	_	2.0	—	ns		

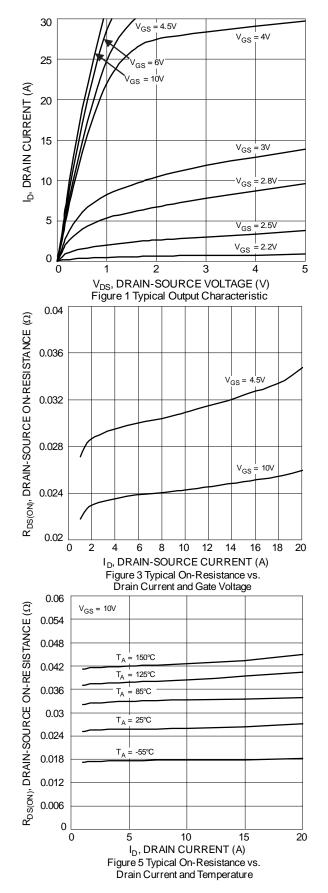
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. 7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}$ C. Notes:

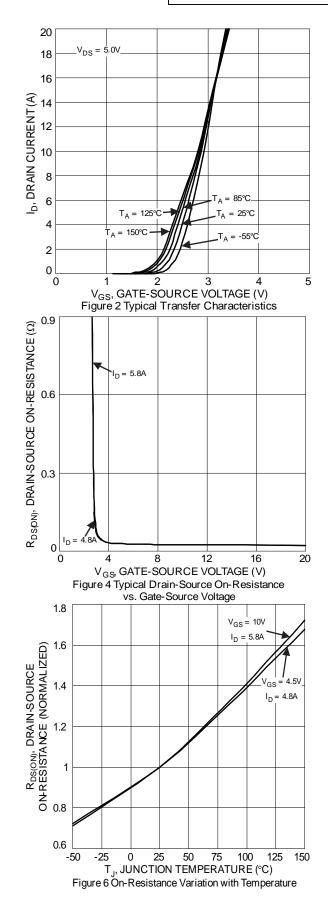
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



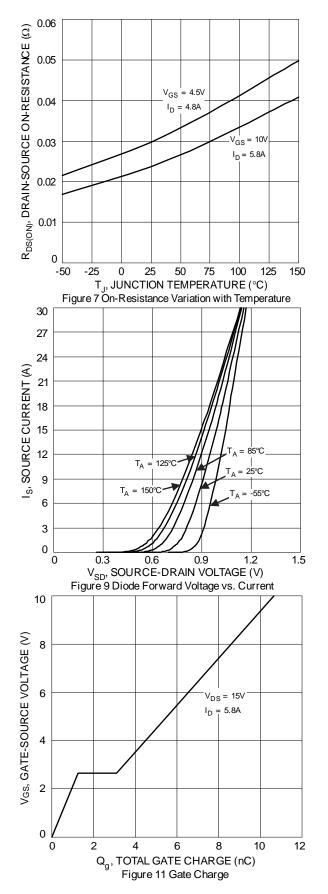
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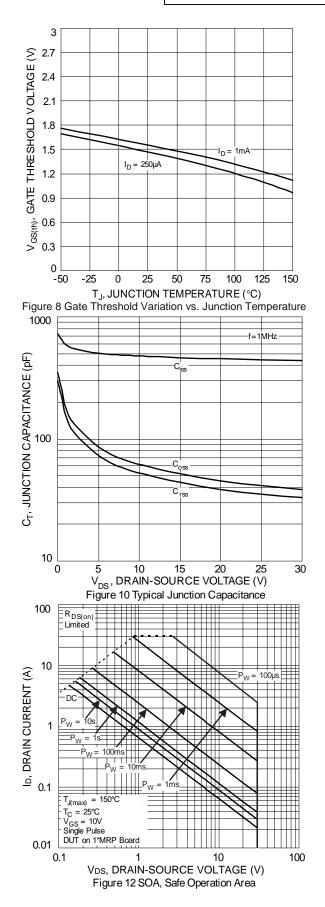




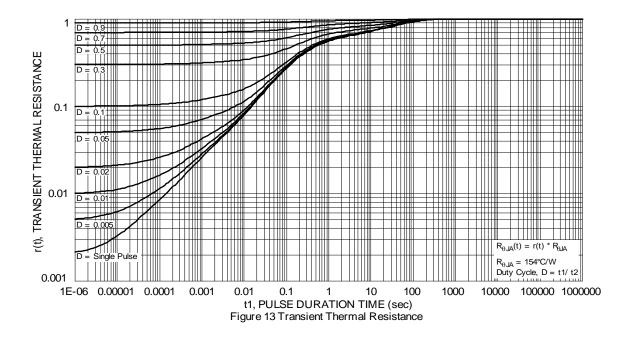
DMN3032LFDBWQ Document number: DS42056 Rev. 2 - 2







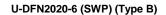


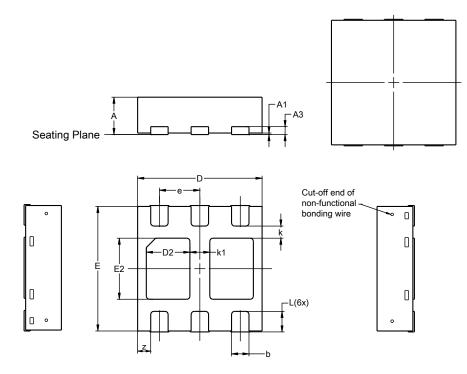




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



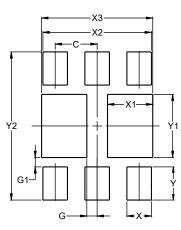


U-DFN2020-6 (SWP)									
Dim	(Type B) Min Max Typ								
A	0.55	0.65	0.60						
A1	0.00	0.05	0.03						
A3			0.127						
b	0.23	0.33	0.28						
D	1.95 2.05 2.00								
D2	0.60	0.80	0.70						
E	1.95 2.05 2.0								
E2	0.88 1.08 0.98								
е	0.65BSC								
k	0.195BSC								
k1	0.32BSC								
L	0.28 0.38 0.33								
z	0.21BSC								
All	All Dimensions in mm								

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (SWP) (Type B)



Dimensions	Value			
Dimensions	(in mm)			
С	0.650			
G	0.160			
G1	0.145			
Х	0.380			
X1	0.700			
X2	1.680			
X3	1.720			
Y	0.515			
Y1	0.980			
Y2	2.300			



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